



2N3055

NPN PLANAR SILICON TRANSISTOR

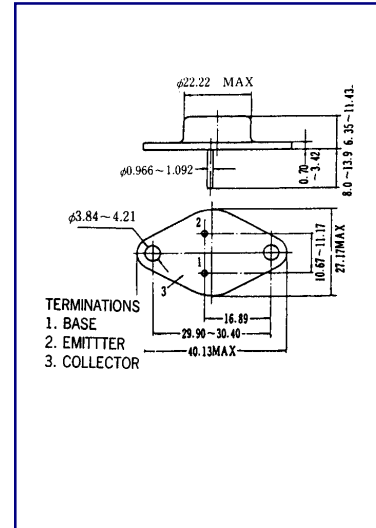
**AUDIO POWER AMPLIFIER
DC TO DC CONVERTER**

TO-3

- High Current Capability
- High Power Dissipation
- Complementary to MJ2955

ABSOLUTE MAXIMUM RATING (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	60	V
Emitter-Base voltage	VEBO	6	V
Collector Current (DC)	IC	15	A
Collector Dissipation	PC	117	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-50~150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BVCBO	IC=10 mA IE=0	60			V
Collector-Emitter Breakdown Voltage	BVCEO	IC=5 mA RBE=∞	60			V
Emitter Base Breakdown Voltage	BVEBO	IE=5 mA IC=0	6			V
Collector Cutoff Current	ICBO	VCE=30V IE=0			0.1	mA
Emitter Cutoff Current	IEBO	VEB=4V IC=0			0.1	mA
*DC Current Gain	hFE1	VCE=5V IC=1A	40		100	
DC Current Gain	hFE2	VCE=5V IC=4A	20		70	
Collector- Emitter Saturation Voltage	VCE(sat)	IC=4A IB=0.4A			1.1	V